

## AMENDMENT TRANSMITTAL LETTER (Large Entity)

Docket No.

OKI.295

Applicant(s): Katsuhito Sasaki

Serial No.  
10/052,244Filing Date  
January 23, 2002Examiner  
J. GarciaGroup Art Unit  
2823Invention: METHOD OF MANUFACTURING LATERAL DOUBLE-DIFFUSED METAL OXIDE  
SEMICONDUCTOR DEVICE

TO THE ASSISTANT COMMISSIONER FOR PATENTS:

An amendment herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

## CLAIMS AS AMENDED

	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST # PREV. PAID FOR	NUMBER EXTRA CLAIMS PRESENT	RATE	ADDITIONAL FEE
TOTAL CLAIMS	18 -	20 =	0	x \$18.00	\$0.00
INDEP. CLAIMS	3 -	3 =	0	x \$84.00	\$0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					\$0.00
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$0.00

- No additional fee is required for amendment.
- Please charge Deposit Account No. \_\_\_\_\_ in the amount of \_\_\_\_\_  
A duplicate copy of this sheet is enclosed.
- A check in the amount of \_\_\_\_\_ to cover the filing fee is enclosed.
- The Commissioner is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account No. 50-0238  
A duplicate copy of this sheet is enclosed.
- Any additional filing fees required under 37 C.F.R. 1.16.
- Any patent application processing fees under 37 CFR 1.17.


  
Signature

Dated: January 21, 2003

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I certify that this document and fee is being deposited on \_\_\_\_\_ with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.

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Typed or Printed Name of Person Mailing Correspondence

CC:



OKI.295

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of

Katsuhito Sasaki

Group Art Unit: 2823

Serial No.: 10/052,244

Examiner: J. Garcia

Filed: January 23, 2002

For: METHOD OF MANUFACTURING LATERAL DOUBLE-DIFFUSED METAL  
OXIDE SEMICONDUCTOR DEVICE

AMENDMENT

Honorable Assistant Commissioner for Patents  
Washington, D.C. 20231

Date: January 21, 2003

Sir:

In response to the Office Action dated November 7, 2002, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

In the Abstract:

Please cancel the Abstract and replace with the Abstract attached herewith.

In the Specification:

Replace the paragraph beginning on page 5, line 7 with the following paragraph:

Subsequently, a first insulating film 104 is formed on the semiconductor substrate 101 of the first conductivity type, and a portion of the first insulating film 104 above the first diffusion layer 103 of the second conductivity type is opened (first

RECEIVED  
JAN 24 2003  
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